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Substitute for form 1449B/PTO <b>INFORMATION DISCLOSURE          STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)			<b>Complete if Known</b>	
			Application Number	10/761,918
Sheet 1 of 1			Filing Date	01/20/2004
			First Named Inventor	Harry A. ATWATER et al.
			Group Art Unit	1764 1765
			Examiner Name	Unassigned Day-Ju Do
			Attorney Docket Number	047071-0107

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
fj	B1	5,013,681		GODBEY et al.	05-07-1991	
	B2	5,217,564		BOZLER et al.	06-08-1993	
	B3	5,391,257		SULLIVAN et al.	02-21-1995	
	B4	5,637,187		TAKASU et al.	06-10-1997	
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		Number			
fj	B22	10/784,586		ATWATER et al.	02/23/2004
	B23	11/004,808		ATWATER et al.	12/07/2004
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	B25	JP	03-270220		FUJITSU LTD.	02-12-1991	Abst.

NON PATENT LITERATURE DOCUMENTS				
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fj	B26	WELDON et al., "Mechanism of Silicon Exfoliation Induced by Hydrogen/Helium Co-Implantation," Applied Physics Letters, Vol. 73, No. 25, December 21, 1998, pgs. 3721-3723.		

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fj

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STATEMENT BY APPLICANT**

Date Submitted: 1/6/05

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**Complete if Known**

Application Number	10/761,918
Filing Date	01/20/2004
First Named Inventor	Harry A. ATWATER et al.
Group Art Unit	1764 <i>PHS</i>
Examiner Name	Unassigned <i>Dwy - Vu Dao</i>
Attorney Docket Number	047071-0107

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<i>JD</i>	A1	5,882,987		SRIKRISHNAN	08/26/1997	
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	A16	WO	01/03172			01/11/2001		

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<i>JD</i>	A19	BRUEL et al., Smart-Cut: A New Silicon On Insulator Material Technology Based on Hydrogen Implantation and Wafer Bonding, March 1997, pp. 1636-1641, Vol. 36, Jpn. J. Appl. Phys	

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				Filing Date	01/20/2004
				First Named Inventor	Harry A. ATWATER et al.
				Group Art Unit	1764
				Examiner Name	Unassigned
Sheet	2	of	7	Attorney Docket Number	047071-0107

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Date Submitted: 1/6/05				<b>First Named Inventor</b>	Harry A. ATWATER et al.
				<b>Group Art Unit</b>	1764
(use as many sheets as necessary)				<b>Examiner Name</b>	Unassigned
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Sheet	3	of	7		

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20	A49	YAMAGUCHI M., Multi-Junction Solar Cells and Novel Structures for Solar Cell Applications, Physica E, 2002, pp. 84-90, Vol. 14, Elsevier Science B.V.	
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70	A51	ZAHLER et al., Wafer Bonded Ge/Si Heterostructures for Photovoltaic Applications, (Presentation), Electronic Materials Conference 2002, 16 pages	

Examiner Signature	70	Date Considered	5/10/06
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  Date Submitted: 1/6/05  (use as many sheets as necessary)		Application Number	10/761,918
		Filing Date	01/20/2004
		First Named Inventor	Harry A. ATWATER et al.
		Group Art Unit	1764
		Examiner Name	Unassigned
Sheet 6 of 7	Attorney Docket Number	047071-0107	

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			

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90	A52	ZAHLER et al., Wafer Bonded Ge/Si Heterostructures for Photovoltaic Applications, (Abstract and Presentation), MRS 2002 Spring Meeting (04/2002)	
1	A53	ZAHLER J.M., Materials Integration by Wafer Bonding and Layer Transfer, (Presentation), 13 pages, MRS 2004 Spring Meeting (04/2004)	
	A54	ZAHLER et al., The Role of H in the H-Induced Exfoliation of GE Films, (Abstract and Presentation), MRS 2004 Spring Meeting, 16 pages (04/2004)	
	A55	ZAHLER et al., Wafer Bonded Expitaxial Templates for GaAs/Si Heterostructures, (Abstract and Presentation), MRS 2003 Spring Meeting, 16 pages, (04/2003)	
	A56	ZAHLER et al., Wafer Bonded Expitaxial Templates for GaAs/Si and InP/Si Heterostructures, (Presentation), MRS 2003 Fall Meeting, 15 pages, (11/2003)	
	A57	ZAHLER et al., Wafer Bonding Processes for Ultrahigh Efficiency Photovoltaic Applications, (Abstract and Presentation), MRS 2001 Fall Meeting, (11/2001)	
	A58	ZAHLER et al., GE Layer Transfer to Si for Photovoltaic Applications, (Presentation), 14 pages, MRS 2001 Spring Conference, (04/2001)	
90	A59	ZAHLER et al., Wafer Bonding and Layer Transfer Processes for A 4-Junction Solar Cell, (Presentation) 29 <sup>th</sup> IEEE Photovoltaic Specialists Conference, New Orleans, USA, (05/2002)	

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Sheet	7	of	7
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JD	A60	ZAHLER et al., Ge/Si Wafer Bonded Epitaxial Templates for GaAs/Si Heterostructures, (Abstract), MRS 2002 Fall Meeting, (11/2002)	
	A61	MORRAL et al., Bonding and Layer Transfer Process of InP on Silicon for the Elaboration of the Bottom Double Heterostructure of 4-Junction High Efficiency Solar Cells, (Abstract), MRS 2002 Fall Meeting, (11/2002)	
	A62	MORRAL et al., Assessment of Optical and Structural Properties of III-V Semiconductors Grown on InP/Si and Ge/Si Wafer Bonded Epitaxial Templates with Application to a Four-Junction Solar Cell, (Abstract), MRS 2003 Spring Meeting, (04/2003)	
	A63	MORRAL et al., Electrical and Structural Characterization of the Interface of Wafer Bonded InP/Si, MRS 2003 Spring Meeting, (04/2003)	
JD	A64	MORRAL et al., The Role of Hydrogen in H-Induced Exfoliation and Layer Transfer on InP, (Abstract), MRS 2004 Spring Meeting, (04/2004)	

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